

SWITCHMODE SERIES NPN POWER TRANSISTORS

... designed for use in high-voltage, high-speed, power switching in inductive circuit, they are particularly suited for 115 and 220 V switchmode applications such as switching regulator's, inverters, DC -DC conveter, Motor control, Solenoid/Relay drivers and deflection circuits.

FEATURES:

*Collector-Emitter Sustaining Voltage-

V_{CEO(SUS)} = 400 V and 300 V * Collector-Emitter Saturation Voltage -

 $V_{CE(sat)} = 1.0 \text{ V (Max.)} \bigcirc I_{C} = 1.0 \text{ A}, I_{B} = 0.25 \text{ A}$ * Switching Time - t_f =0.7 us (Max.) $\bigcirc I_{C} =1.0 \text{ A}$

MJE13002 MJE13003

1.5 AMPERE **POWER TRANASISTORS** 300-400 VOLTS 40 WATTS

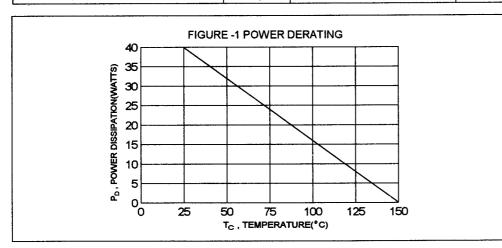
NPN

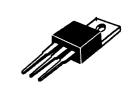
MAXIMUM RATINGS

Characteristic	Symbol	MJE13002	MJE13003	Unit
Collector-Emitter Voltage	V _{CEO}	300	400	V
Collector-Emitter Voltage	V _{CEV}	600	700	٧
Emitter-Base Voltage	V _{EBO}	9.0		٧
Collector Current - Continuous - Peak	I _C	1.5 3.0		Α
Base current	l _B	0.75		Α
Total Power Dissipation @T _C = 25°C Derate above 25°C	P _D	40 0.32		W/°C
Operating and Storage Junction Temperature Range	T _J ,T _{STG}	-65 to +150		°C

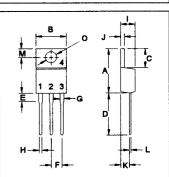
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance Junction to Case	Rθjc	3.12	°C/W





TO-220



PIN 1.BASE 2.COLLECTOR 3.EMITTER 4.COLLECTOR(CASE)

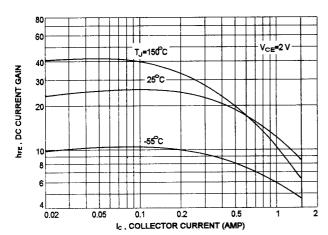
D144	MILLIMETERS			
DIM	MIN	MAX		
Α	14.68	15.31		
В	9.78	10.42		
С	5.01	6.52		
D	13.06	14.62		
E	3.57	4.07		
F	2.42	3.66		
G	1.12	1.36		
Н	0.72	0.96		
ı	4.22	4.98		
J	1.14	1.38		
K	2.20	2.97		
L	0.33	0.55		
M	2.48	2.98		
0	3.70	3.90		

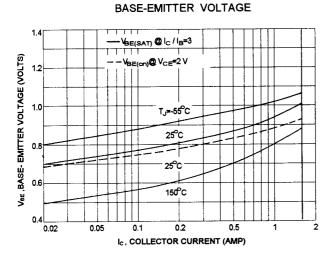
ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Charac	teristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Sustaining Vol (I _C = 10 mA, I _B = 0)	tage MJE13002 MJE13003	V _{CEO(sus)}	300 400		V
Collector Cutoff Current (V _{CEV} = Rated Value, V _{BE(off)} =1 (V _{CEV} = Rated Value, V _{BE(off)} =1	.5 V) .5 V , T _C =100 °C)	ICEV		1.0 5.0	mA
Emitter Cutoff Current (V _{EB} = 9.0 V, I _C = 0)		I _{EBO}		1.0	mA
ON CHARACTERISTICS (1)					
DC Current Gain (I _c = 0.5 A, V _{CE} = 2.0V) (I _c = 1.0 A, V _{CE} = 2.0V)		hFE	8.0 5.0	40 25	
Collector-Emitter Saturation Vol $(I_c=0.5 \text{ A}, I_B=100 \text{ mA})$ $(I_c=1.0 \text{ A}, I_B=250 \text{ mA})$ $(I_c=1.5 \text{ A}, I_B=0.5 \text{ A})$	tage	V _{CE(sat)}		0.5 1.0 3.0	V
Base-Emitter Saturation Voltage (I _C = 0.5 A, I _B = 100 mA) (I _C = 1.0 A, I _B = 250 mA)	}	V _{BE(sat)}		1.0 1.2	V
DYNAMIC CHARACTERISTI	CS				
Current Gain - Bandwidth Produ (I _C = 100 mA , V _{CE} = 10 V ,f =		f _T	4.0		MHz
SWITCHING CHARACTERIS	TICS				
Delay Time	V _{CC} = 125 V, I _C = 1.0 A	t _d		0.1	us
Rise Time	I _{R1} = -I _{R2} =0.2A,	t,		1.0	us
Storage Time	tp = 25 us,Duty Cycle ≦1 %	ts		4.0	us
Fall Time		t,		0.7	us

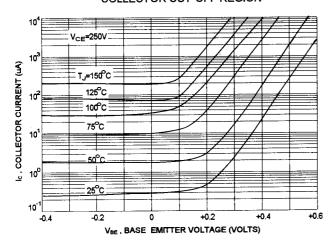
⁽¹⁾ Pulse Test: Pulse Width =300 us, Duty Cycle $\leq 2.0\%$

DC CURRENT GAIN

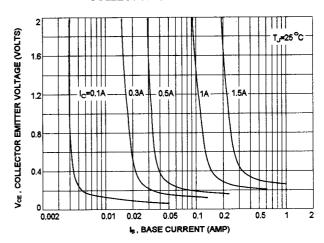




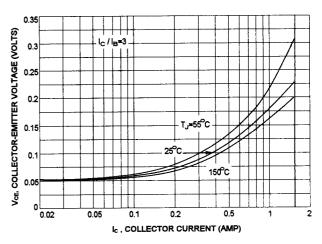
COLLECTOR CUT-OFF REGION



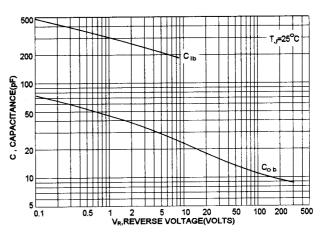
COLLECTOR SATURATION REGION

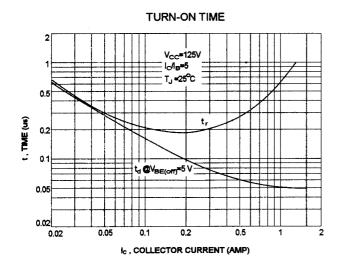


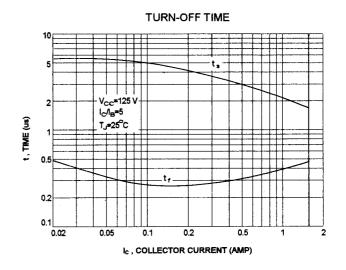
COLLECTOR-EMITTER SATURATION VOLTAGE



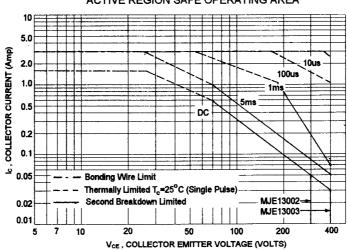
CAPACITANCE







ACTIVE REGION SAFE OPERATING AREA



REVERSE BIAS SWITCHING SAFE OPERATING AREA

